



STP80NF55-08 STB80NF55-08 STB80NF55-08-1

N-CHANNEL 55V - 0.0065 Ω - 80A D²PAK/I²PAK/TO-220
STripFET™ II POWER MOSFET

Table 1: General Features

TYPE	V _{DSS}	R _{DS(on)}	I _D
STB80NF55-08/-1	55 V	<0.008 Ω	80 A
STP80NF55-08	55 V	<0.008 Ω	80 A

- TYPICAL R_{DS(on)} = 0.0065 Ω
- LOW THRESHOLD DRIVE

DESCRIPTION

This Power MOSFET is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

APPLICATIONS

- HIGH CURRENT SWITCHING APPLICATION
- AUTOMOTIVE ENVIRONMENT

Figure 1: Package

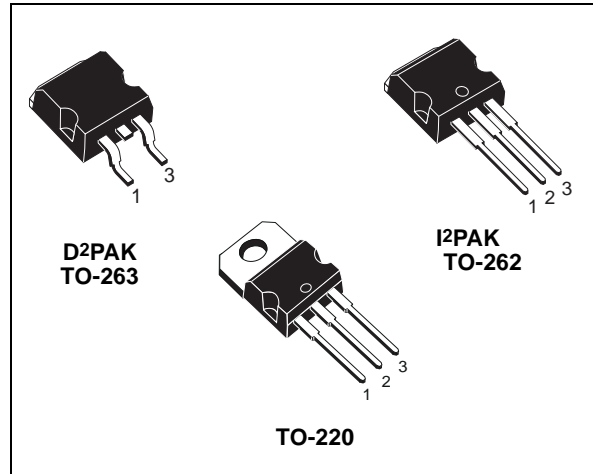


Figure 2: Internal Schematic Diagram

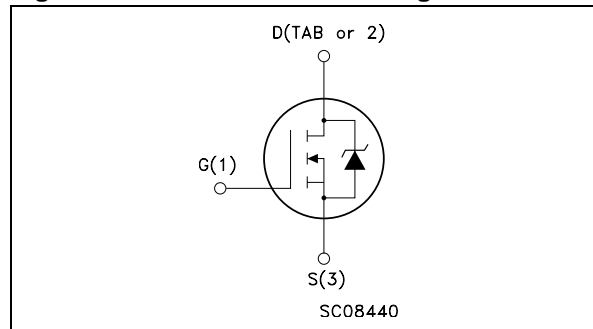


Table 2: Order Codes

SALES TYPE	MARKING	PACKAGE	PACKAGING
STB80NF55-08-1	B80NF55-08	I ² PAK	TUBE
STB80NF55-08T4	B80NF55-08	D ² PAK	TAPE & REEL
STP80NF55-08	P80NF55-08	TO220	TUBE

Table 3: ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	55	V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 k Ω)	55	V
V _{GS}	Gate- source Voltage	± 20	V
I _D (●)	Drain Current (continuous) at T _C = 25°C	80	A
I _D (●)	Drain Current (continuous) at T _C = 100°C	80	A
I _{DM} (●●)	Drain Current (pulsed)	320	A
P _{tot}	Total Dissipation at T _C = 25°C	300	W
	Derating Factor	2	W/°C
E _{AS} (¹)	Single Pulse Avalanche Energy	870	mJ
T _{stg}	Storage Temperature	-55 to 175	°C
T _j	Operating Junction Temperature		

(●●) Pulse width limited by safe operating area.

(●) Current limited by package

(1) Starting T_j = 25 °C, I_D = 40A, V_{DD} = 30V

STB80NF55-08/-1 STP80NF55-08**Table 4: THERMAL DATA**

Rthj-case	Thermal Resistance Junction-case	Max	0.5	°C/W
Rthj-amb	Thermal Resistance Junction-ambient	Max	62.5	°C/W
T _l	Maximum Lead Temperature For Soldering Purpose	Typ	300	°C

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)**Table 5: OFF**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 μA V _{GS} = 0	55			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating T _C = 125°C			1 10	μA μA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 20V			±100	nA

Table 6: ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} I _D = 250 μA	2	3	4	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10 V I _D = 40 A		0.0065	0.008	Ω

Table 7: DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (*)	Forward Transconductance	V _{DS} = 15 V I _D = 18 A		40		S
C _{iSS}	Input Capacitance	V _{DS} = 25V, f = 1 MHz, V _{GS} = 0		3850		pF
C _{oSS}	Output Capacitance			800		pF
C _{rSS}	Reverse Transfer Capacitance			250		pF

ELECTRICAL CHARACTERISTICS (continued)

Table 8: SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Delay Time Rise Time	$V_{DD} = 30\text{ V}$ $I_D = 40\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$ (Resistive Load, Figure 17)		25 85		ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 44\text{ V}$ $I_D = 80\text{ A}$ $V_{GS} = 10\text{ V}$		115 24 46	155	nC nC nC

Table 9: SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$ t_f	Turn-off Delay Time Fall Time	$V_{DD} = 30\text{ V}$ $I_D = 40\text{ A}$ $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ (Resistive Load, Figure 17)		70 25		ns ns

Table 10: SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM} (*)$	Source-drain Current Source-drain Current (pulsed)				80 320	A A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 80\text{ A}$ $V_{GS} = 0$			1.5	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 80\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 25\text{ V}$ $T_j = 150^\circ\text{C}$ (see test circuit, Figure 19)		80 245 6.4		ns nC A

(*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.
 (●) Pulse width limited by safe operating area.

Figure 3: Safe Operating Area

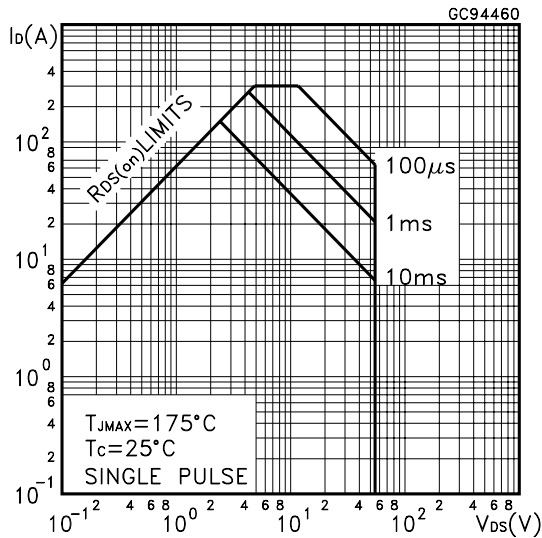


Figure 4: Thermal Impedance

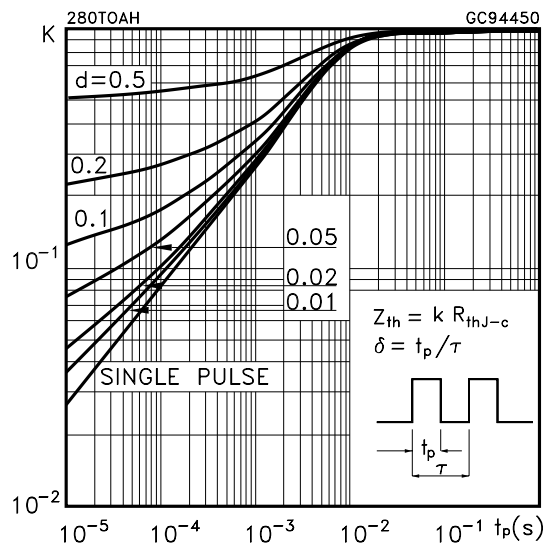


Figure 5: Output Characteristics

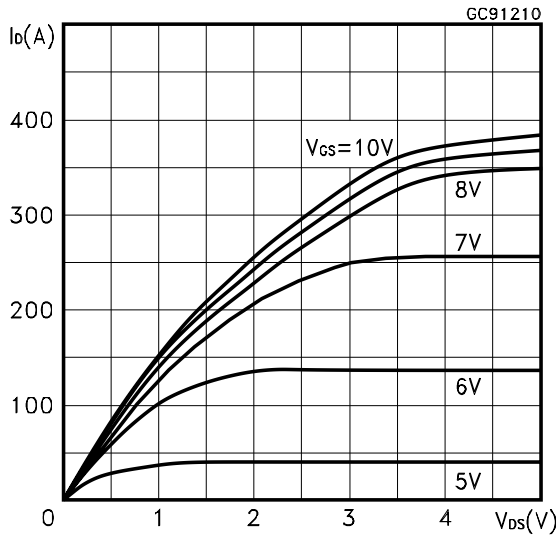


Figure 7: Transconductance

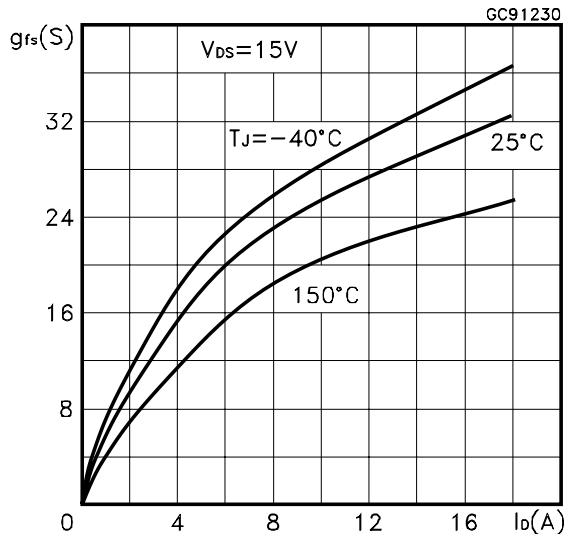


Figure 9: Gate Charge vs Gate-source Voltage

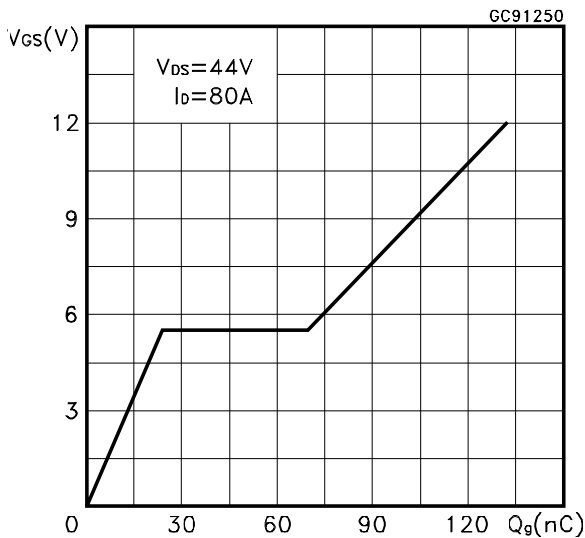


Figure 6: Transfer Characteristics

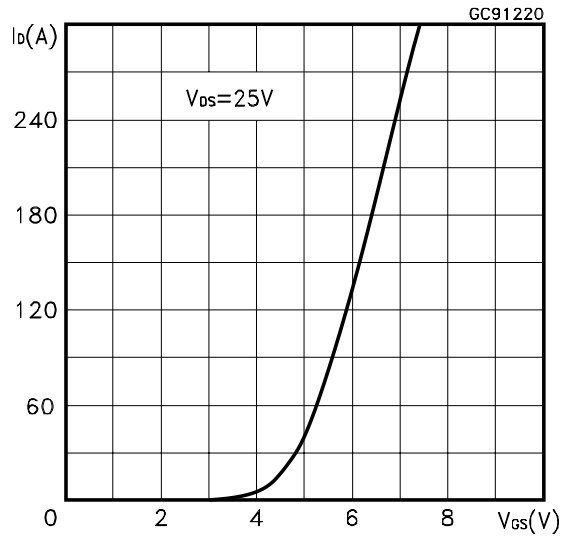


Figure 8: Static Drain-source On Resistance

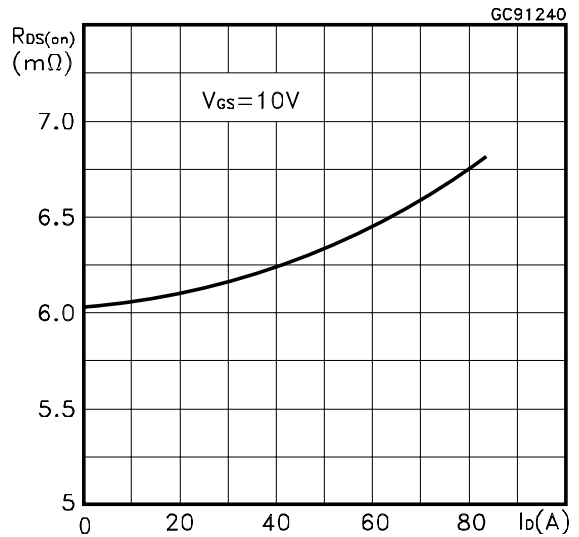


Figure 10: Capacitance Variations

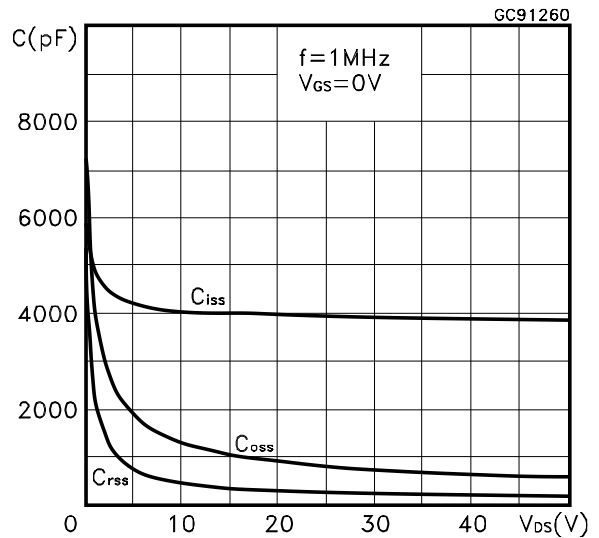


Figure 11: Normalized Gate Threshold Voltage vs Temperature

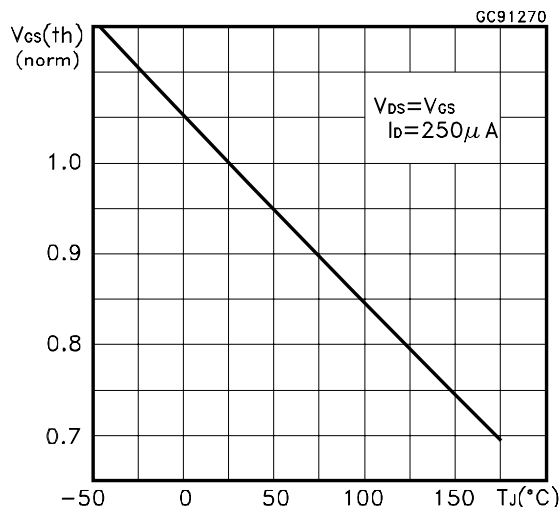


Figure 13: Source-drain Diode Forward Characteristics

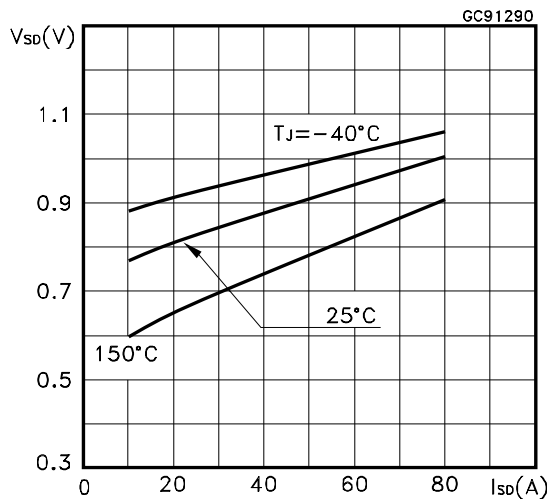


Figure 12: Normalized on Resistance vs Temperature

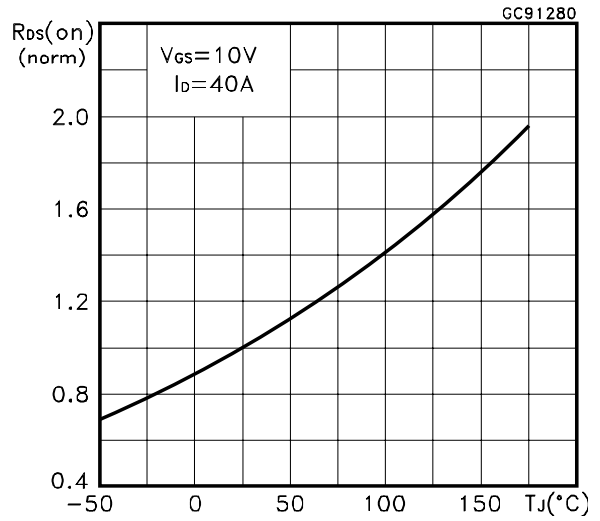


Figure 14: Normalized Breakdown Voltage vs Temperature.

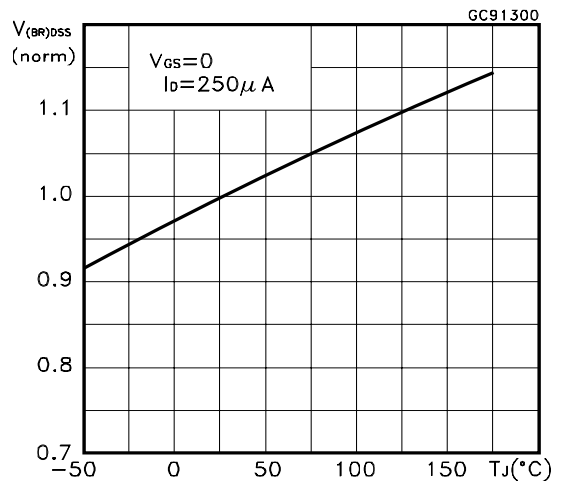


Figure 15: Unclamped Inductive Load Test Circuit

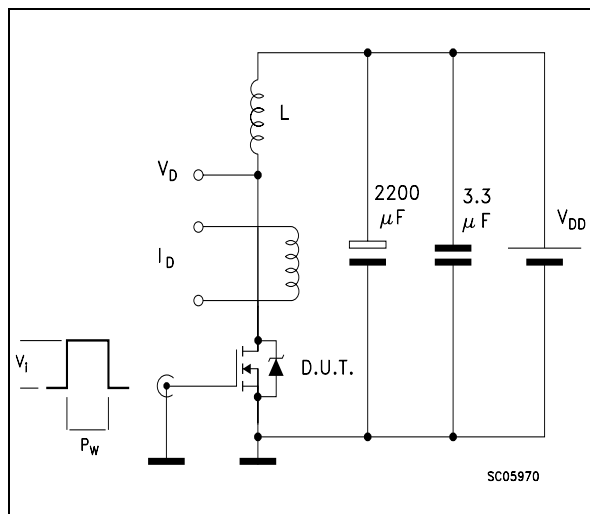


Figure 16: Unclamped Inductive Waveform

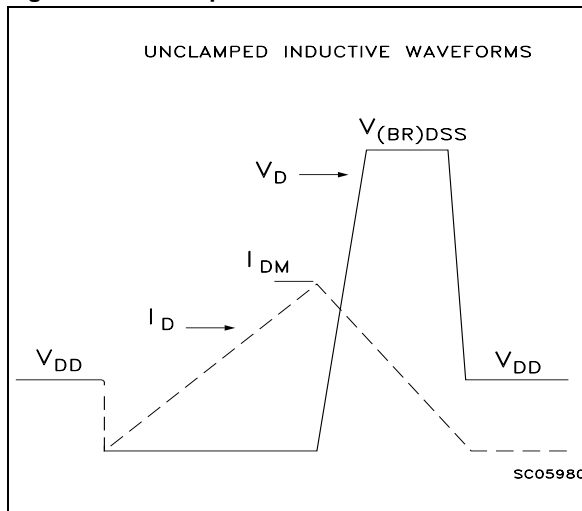


Figure 17: Switching Times Test Circuits For Resistive Load

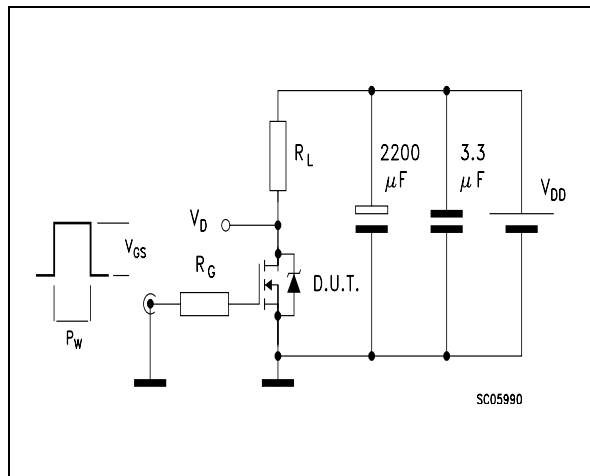


Figure 18: Gate Charge test Circuit

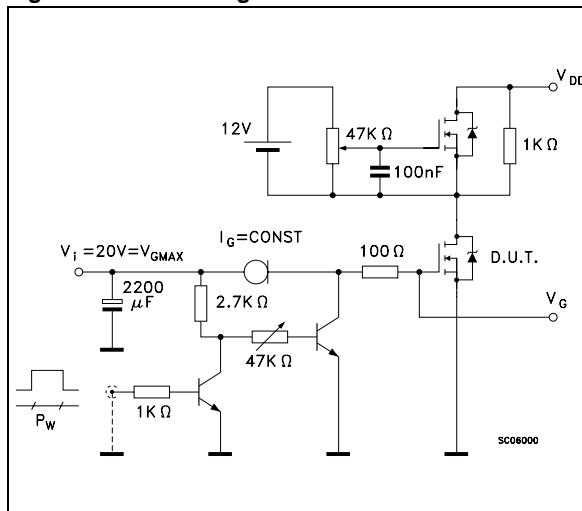
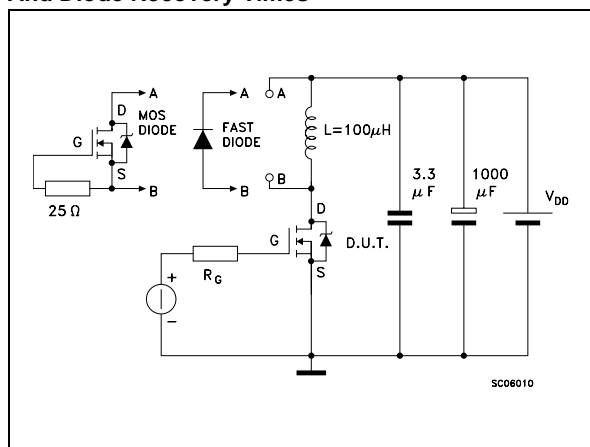
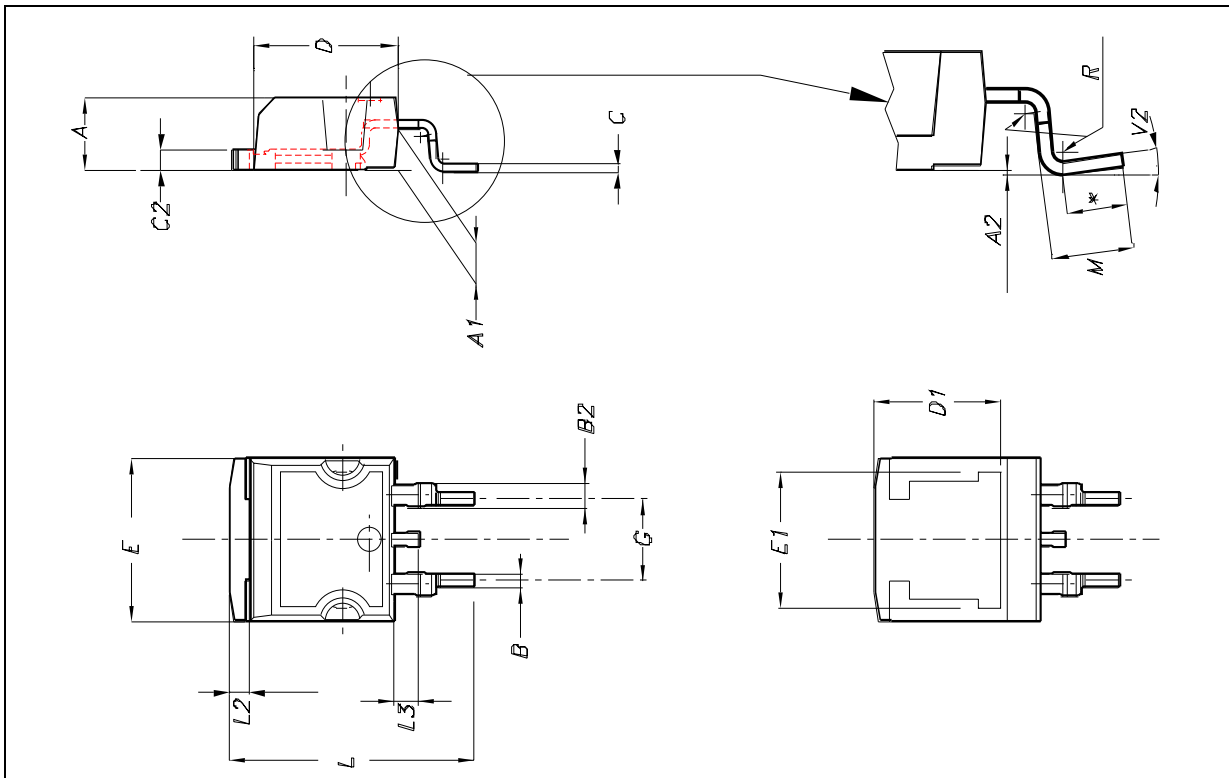


Figure 19: Test Circuit For Inductive Load Switching And Diode Recovery Times



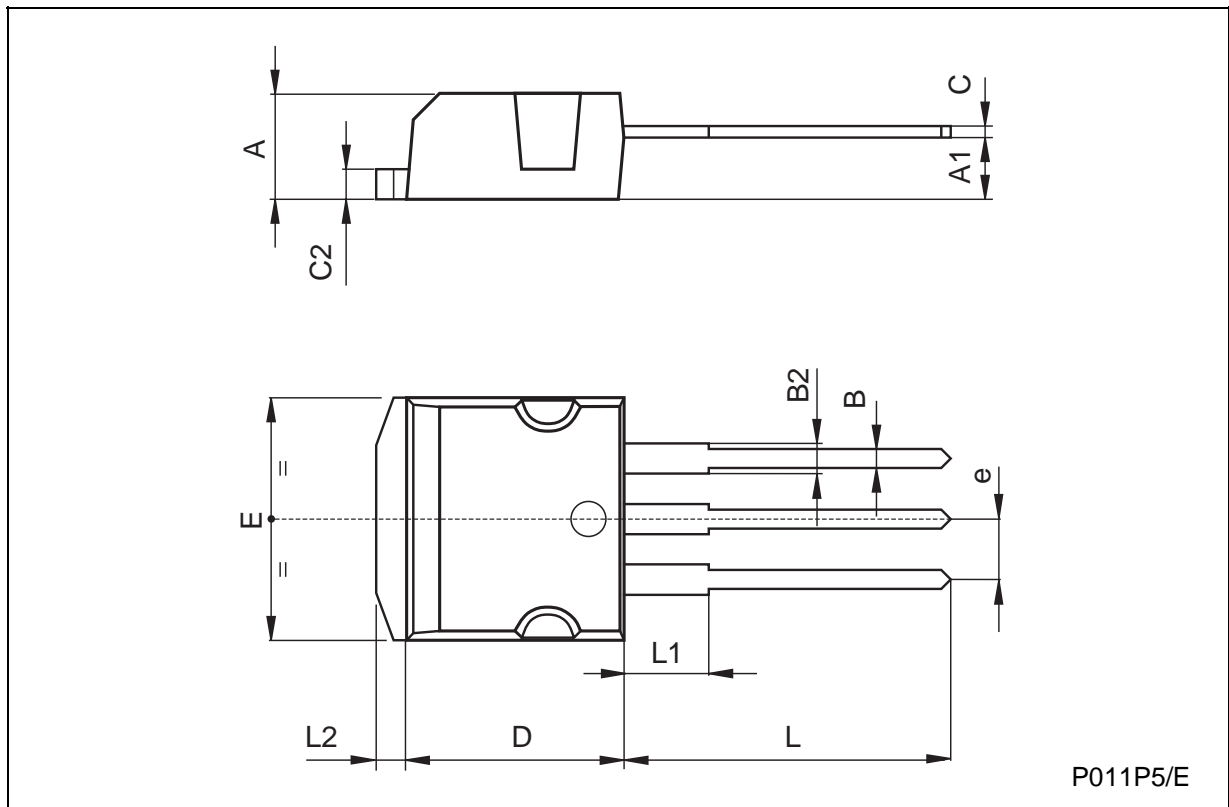
D²PAK MECHANICAL DATA

DIM.	mm.			inch.		
	MIN.	TYP.	MAX.	MIN.	TYP.	TYP.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.028		0.037
B2	1.14		1.7	0.045		0.067
C	0.45		0.6	0.018		0.024
C2	1.21		1.36	0.048		0.054
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.394		0.409
E1	8.5				0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.591		0.624
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.069
M	2.4		3.2	0.094		0.126
R		0.4			0.016	
V2	0°		8°	0°		8°



TO-262 (I²PAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
e	2.4		2.7	0.094		0.106
E	10		10.4	0.393		0.409
L	13.1		13.6	0.515		0.531
L1	3.48		3.78	0.137		0.149
L2	1.27		1.4	0.050		0.055

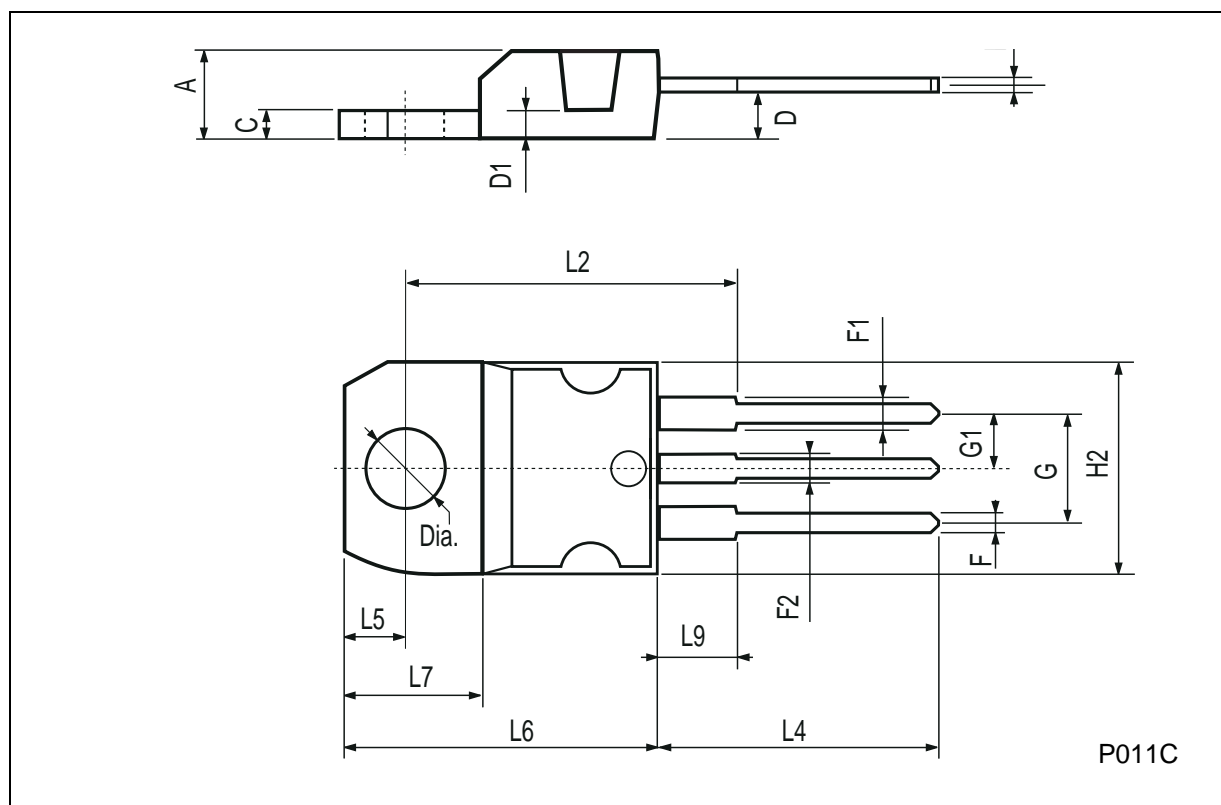


P011P5/E

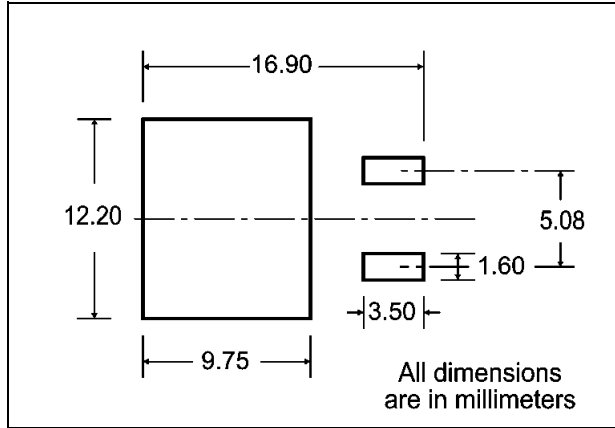


TO-220 MECHANICAL DATA

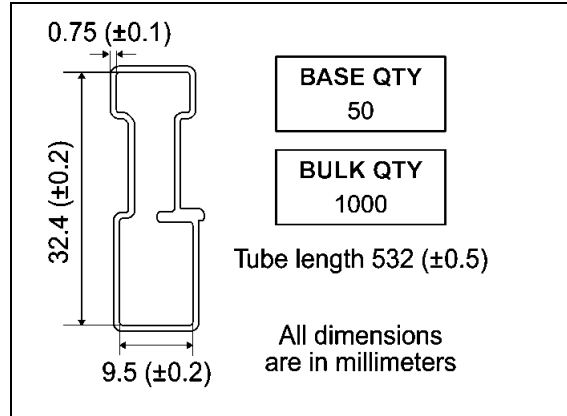
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



D2PAK FOOTPRINT



TUBE SHIPMENT (no suffix)*



TAPE AND REEL SHIPMENT (suffix "T4")*

REEL MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

BASE QTY	BULK QTY
1000	1000

TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956

* on sales type

Table 11:Revision History

Date	Revision	Description of Changes
January 2005	1.0	FIRST ISSUE

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